PREPARED BY:	DATE:			SPEC No ED-95093
J. Oka	August 4,1995	SHAR	P	ISSUE August 4, 1995
APPROVED BY:	DATE:			PAGE 7 Pages
J. Jshizabi	August 4.198	ELECTRONIC COMPO GROUP SHARP CORP	1	REPRESENTATIVE DIVISION
<u> </u>		SPECIFICAT	ION	OPTO-ELECTRONIC DEVICES DIV.
		CE SPECIFICATION FOR INFRARED EMITTING EL No. GL1F201	DIODE	
		GE11 201		
				
2. Pl S	lease obey the instance of the second of the	eproduce them without Sharp's contructions mentioned below for accessorsibility for damage caused by designed for general electronic exhis device are as follows: OA equipment • Telecommunic equipment • Tooling machine oper steps in order to maintain reconstructions and safety of a vehicul • Gas leak detection breaker equipment, etc. Use for the uses mentioned below ment • Telecommunication equipment equipment • Medical equipment equipment • Medical equipment experience of the safety of the uses mentioned below ment • Telecommunication equipment • Medical equ	ctual use of this by improper use quipment. AV equipmer eliability and sa quire high relial le (air plane, tra Fire box and which require	oment (Terminal) nt • Home appliance, etc afety, in case this device ability. rain, automobile etc.) nd burglar alarm box e extremely high reliability.
d		representative of sales office in ac plications other than those applic ARP at (1).	-	
CUSTON	MER'S APPROV	AL	DATE PRESENTEI BY	D K.E
DATE	:		Opto-S	Manager System Project Team
В У	,		ELECO	Electronic Devices Div. DM Group P CORPORATION

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1. Application

This specification applies to the outline and characteristics of GaAlAs type chip infrared emitting diode Model No. GL1F201.



2. Outline

Refer to the attached drawing No. CY8077i02.

3. Ratings and characteristics

Refer to the attached sheet, page 4, 5.

4. Reliability

Refer to the attached sheet, page 6.

5. Incoming inspection

Refer to the attached sheet, page 7.

6. Supplement

7. Notes

- (1) In circuit designing, make allowance for the degradation of the light emitting diode output that results from long continuous operation. (MAX. 50% degradation/ 5 years)
- (2) Cleaning conditions:

Solvent cleaning: Solvent temperature 45 'C or less

Immersion for 3 min or less

Ultrasonic cleaning: The affect to device by ultrasonic cleaning is different

by cleaning bath size, ultrasonic power

output, cleaning time, PCB size or device mounting condition etc. Please test it in actual using condition and confirm that doesn't occur any defect before starting

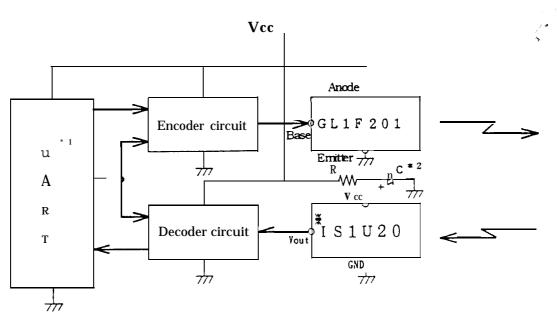
the ultrasonic cleaning.

The cleaning shall be carried out with solvent below.

Solvent: Ethyl alcohol, Methyl alcohol, Isopropyl alcohol

(3) The lead pins should be soldered according to the absolute maximum ratings. While or after soldering, the lead pins shall be free from physical stress. This device shall not be soldered with preheat or reflow.

(4) Example of system

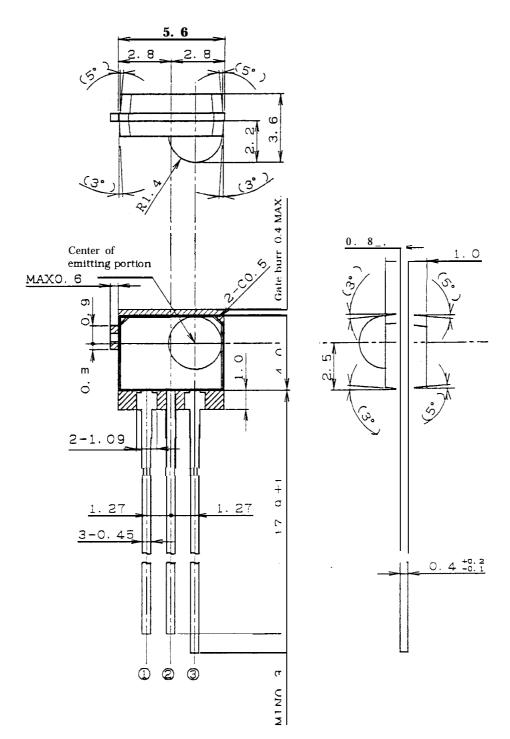


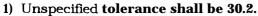
- *1 UART (Universal Asynchronous Receiver/Transmitter)
- •2 Please choose the most suitable C and R according to the noise level and noise frequency of power supply. Example: $C=47 \mu F$, $R=47 \Omega$

We recommended to use IS 1U20 as detecting device.

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2) Dimensions in parenthesis are shown for reference.

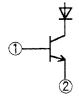
3) area: Burr

4) Resin burr shall not be included in outline dimensions.

5) Package: Transparent

6) Pin arrangement





7) Lead pitch distance denotes that of the lead root.

Scale		Material	Finish		GL1F201
3/1	4	Lead :Cu	Lead : Solder dip	Name	Outline Dimensions
1=1/1mm	I	Package : Epoxy resin		Drawing No.	CY8077i02

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3. Ratings and characteristics

3.1 Absolute maximum ratings

Ta=25℃



Parameter	symbol	Rating	unit
Forward current	I _F	50	mA
* 1 Peak forward current	I _{FM}	400	mA
Operating temperature	Topr	-10 to +70	"c
Storage temperature	Tstg	-20 to +85	"c
*2 Soldering temperature	Tsol	260	Ç

^{*1} Pulse width : 78.1 μ s, Duty ratio : 3/16

3.2 Electro-optical characteristics

Ta=25℃

Parameter	Parameter symbol MIN. TYP. MAX. unit		Conditions				
Radiant intensity	$I_{\rm E}$	40		350 mW/sr			
Rise time	tr		0.09	0066	μs	$V_{IN} = 2.7V *3$ $R_{B} = 1k \Omega \pm 5\%$	
Fall time	tf		0.21 0066		μS	C _B =1500pF t _{WIN} =1.63 μs DR=3/16	
Pulse width	tw	1.41	1.7	2.71	μιs	$ \rho \leq 15^{\circ} *4 $	
Operating voltage	Vcc	2.7	_	3.3	¥		
High level input voltage	V _{IH}	2.7	-	Vcc	v		
Low level input voltage	V_{IL}		-	0.4	V		
Input current	I _{IH}	1.3	-	2.4	mA	V _{IN} =2.7V *3	
Peak emission wavelength	λр	850	870	900	nm	I _F =20mA	
Spectrum radiation bandwidth	Δλ		40	-	nm	I _F =20mA	
Half intensity angle	Δθ		±20	-		I _F =20mA	

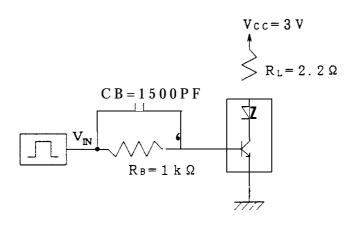
^{*3} Refer to the Recommended circuit

^{*2} For 3 s MAX. at the position of 2mm from the resin edge.

^{*4} It is ϕ =0" in the direction of mechanical axis of lens portion.

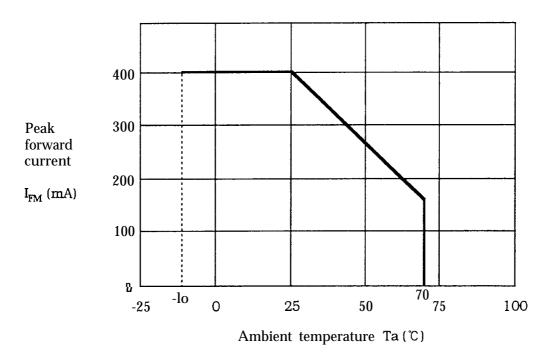
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• Recommended circuit



(3.3) Peak forward current vs. ambient temperature

Pulse width $\leq 78.1 \,\mu$ s, Duty ratio 3/16



		
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4. Reliability

The reliability of products shall be satisfied with items listed below.

Confidence level: 90%

LTPD: 20%

Test Items	Test Conditions	Failure Judgement Criteria	Samples (n) Defective(C)
Temperature cycling	1 cycle -20°C ←→+85°C (30min) (30min) 20 cycles test		n=11, C=O
High temp. and high humidity storage	+60℃,90%RH, 240h	L×0.8≦I _E	n=11, C=0
High temp. storage	+85°C, 240h	≦U×1.2 tr≦U×1.2	n=11, C=0
Low temp. storage	-20℃, 240h	tf≦U×1.2	n=11, C=0
Operation life	Ta=25°C, I _{FM} =400mA t _{WIN} =78.1 μs, DR=3/16, 240h	L×0.8 ≤tw ≤U×1.2	n=11, C=0
Mechanical shock	1000m/s^2 , 6ms, Half sine wave 3 times/ $\pm X$, $\pm Y$, $\pm Z$ direction		n=11, C=0
Variable frequency vibration	200m/s ² 100 to 2000 to 100HZ /Approx. for 4min 48 rein/X, Y, Z direction	U: Upper specification limit	n=11, C=0
Terminal strength (Tension)	Weight: 5.0N 10 s/each terminal	L: Lower specification	n=11, C=O
Terminal strength (Bending)	Weight: 2.5N 0' →90' →0' →-90' →0' 2 times bending	limit	n=11, C=O
Soldering heat	260±5℃, 3 S		n=11, C=0
Solderability	230±5℃, 5 S Prior disposition: Diped position is shown in parameter 3.1 *2.	Solder shall be adhere at the area of 95% or more of dipped portion.	n=11, C=O

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5. Incoming inspection

(1) Inspection lot

Inspection shall be carried out per each delivery lot.

(2) Inspection method

A single sampling plan, normal inspection level ${
m I\hspace{-.1em}I}$ based on MIL-STD- 105D shall be adopted.

Parameter		Inspection items and test method							
	1	Disconnection, short							
	2	Inverse polarity on terminal							
	3	Soldering defect (Obstacle to use)							
	4	Characteristics defect							
Major defect		Parameter	symbol	Judgemer MIN	nt criteria MAX.	unit	0.1		
delect		Radiant intensity	$I_{\mathbf{E}}$	40	350	mW/sr	0.1		
		Rise time	tr		0.6	μs			
		Fall time	tf		0.6	μs			
		Pulse width	tw	1.41	2.71	/us			
		Test conditions refe	r to parame	eter 3.2.					
	1	Appearance defect							
		Parameter	Judgement criteria						
	Split, chip, Scratch, Stain, Blur		Visible cra position sl						
Minor defect			One which of parame	0.4					
		Bubble Foreign matter (One on resin surface which can wipe off shall not be applied.)	 On light detector One which affects the characteristics of parameter 3.2 shall be defect. Area excepting on light detector 1.0mm \$\phi\$ or more shall be defect. 						